

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Canceled)

2. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate, each pixel comprising a first thin film transistor;

a data line driver circuit over the substrate, comprising a second thin film transistor; [[and]]

an insulating film over the first thin film transistor and the second thin film transistor;

a film comprising a metal having a light shielding property, and overlapping the first thin film transistor through the insulating film;

a dividing circuit over the substrate, for dividing a signal into n signals, and ~~inputting the n signals to n pixels among the plurality of pixels through~~ outputting the n signals to n video input signal lines,

wherein the n signals are inputted into ~~[[the]]~~ n first thin film transistors corresponding to n pixels among the plurality of pixels by a timing signal supplied from the data driver circuit, simultaneously, and

wherein wirings of the data line driver circuit and the dividing circuit comprise the metal.

3. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate, each pixel comprising a first thin film transistor;

a data line driver circuit comprising a plurality of NAND circuits over the substrate, each NAND comprising a second thin film transistor; [[and]]

an insulating film over the first thin film transistor and the second thin film transistor;

a film comprising a metal having a light shielding property, and overlapping the first thin film transistor through the insulating film;

a dividing circuit over the substrate, for dividing a signal into n signals, and ~~inputting the n signals to n pixels among the plurality of pixels through~~ outputting the n signals to n video input signal lines,

wherein the n signals are inputted into ~~[[the]]~~ n first thin film transistors corresponding to n pixels among the plurality of pixels by a timing signal supplied from one of the plurality of NAND circuits, simultaneously, and

wherein wirings of the data line driver circuit and the dividing circuit comprise the metal.

4. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate, each pixel comprising a first thin film transistor;

a data line driver circuit over the substrate, and comprising a second thin film transistor;

an insulating film over the first thin film transistor and the second thin film transistor;

a film comprising a metal having a light shielding property, and overlapping the first thin film transistor through the insulating film;

a dividing circuit over the substrate, for dividing three signals corresponding to colors R, G and B into $3n$ signals, and ~~inputting the $3n$ signals to $3n$ pixels among the plurality of pixels through~~ outputting the $3n$ signals to $3n$ video input signal lines,

wherein the 3n signals are inputted into [[the]] 3n first thin film transistors corresponding to 3n pixels among the plurality of pixels by a timing signal supplied from the data driver circuit, simultaneously, and

wherein wirings of the data line driver circuit and the dividing circuit comprise the metal.

5. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate, each comprising a first thin film transistor;

a data line driver circuit comprising a plurality of NAND circuits, each NAND comprising a second thin film transistor over the substrate; and

an insulating film over the first thin film transistor and the second thin film transistor;

a film comprising a metal having a light shielding property, and overlapping the first thin film transistor through the insulating film;

a dividing circuit over the substrate, for dividing three signals corresponding to colors R, G and B ~~into 3n signals~~ into 3n signals, and ~~inputting the 3n signals to 3n pixels among the plurality of pixels through~~ outputting the 3n signals to 3n video input signal lines,

wherein the 3n signals are inputted into [[the]] 3n first thin film transistors corresponding to 3n pixels among the plurality of pixels by a timing signal supplied from one of the plurality of NAND circuits, simultaneously, and

wherein wirings of the data line driver circuit and the dividing circuit comprise the metal.

6. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate, each of the plurality of pixels having a first thin film transistor;

a data line driver circuit over the substrate, and comprising a second thin film transistor; and

a first insulating film over the first thin film transistor and the second thin film transistor;

a second insulating film over the first insulating film;

a film comprising a metal having a light shielding property, provided over the second insulating film, and overlapping the first thin film transistor;

a dividing circuit over the substrate, for dividing a signal into n signals, and ~~inputting the n signals to n thin film transistors corresponding to n pixels among the plurality of pixels through~~ outputting the n signals to n video input signal lines,

wherein the n signals are inputted into [[the]] n first thin film transistors corresponding to n pixels among the plurality of pixels by a timing signal supplied from the data driver circuit, simultaneously, and

wherein wirings of the data line driver circuit and the dividing circuit comprise the metal.

7. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate, each of the plurality of pixels having a first thin film transistor;

a data line driver circuit comprising a plurality of NAND circuits over the substrate, each NAND comprising a second thin film transistor; and

a first insulating film over the first thin film transistor and the second thin film transistor;

a second insulating film over the first insulating film;

a film comprising a metal having a light shielding property, provided over the second insulating film, and overlapping the first thin film transistor;

a dividing circuit over the substrate, for dividing a signal into n signals, and ~~inputting the n signals to n thin film transistors corresponding to n pixels among the plurality of pixels through~~ outputting the n signals to n video input signal lines,

wherein the n signals are inputted into ~~[[the]]~~ n first thin film transistors corresponding to n pixels among the plurality of pixels by a timing signal supplied from one of the plurality of NAND circuits, simultaneously, and

wherein wirings of the data line driver circuit and the dividing circuit comprise the metal.

8. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate, each of the plurality of pixels having a first thin film transistor;

a data line driver circuit over the substrate, and comprising a second thin film transistor;

a first insulating film over the first thin film transistor and the second thin film transistor;

a second insulating film over the first insulating film;

a film comprising a metal having a light shielding property, provided over the second insulating film, and overlapping the first thin film transistor;

a dividing circuit over the substrate, for dividing three signals corresponding to colors R, G and B into $3n$ signals, and ~~inputting the $3n$ signals to $3n$ thin film transistors corresponding to $3n$ pixels among the plurality of pixels through~~ outputting the $3n$ signals to $3n$ video input signal lines,

wherein the $3n$ signals are inputted into ~~[[the]]~~ $3n$ first thin film transistors corresponding to $3n$ pixels among the plurality of pixels by a timing signal supplied from the data driver circuit, simultaneously, and

wherein wirings of the data line driver circuit and the dividing circuit comprise the metal.

9. (Currently Amended) A semiconductor device comprising:

a plurality of pixels over a substrate, each of the plurality of pixels having a first thin film transistor;

a data line driver circuit comprising a plurality of NAND circuits over the substrate, each NAND comprising a second thin film transistor; ~~[[and]]~~

a first insulating film over the first thin film transistor and the second thin film transistor;

a second insulating film over the first insulating film;

a film comprising a metal having a light shielding property, provided over the second insulating film, and overlapping the first thin film transistor;

a dividing circuit over the substrate, for dividing three signals corresponding to colors R, G and B into 3n signals, and ~~inputting the 3n signals to 3n thin film transistors corresponding to 3n pixels among the plurality of pixels through~~ outputting the 3n signals to 3n video input signal lines,

wherein the 3n signals are inputted into ~~[[the]]~~ 3n first thin film transistors corresponding to 3n pixels among the plurality of by a timing signal supplied from one of the plurality of NAND circuits, simultaneously, and

wherein wirings of the data line driver circuit and the dividing circuit comprise the metal.

10. (Previously Presented) A semiconductor device according to claim 2, wherein the data line driver circuit comprises a shift register, NAND circuits, a level shifter and a buffer.

11. (Previously Presented) A semiconductor device according to claim 3, wherein the data line driver circuit further comprises a shift register, a level shifter and a buffer.

12. (Previously Presented) A semiconductor device according to claim 4, wherein the data line driver circuit comprises a shift register, NAND circuits, a level shifter and a buffer.

13. (Previously Presented) A semiconductor device according to claim 5, wherein the data line driver circuit further comprises a shift register, a level shifter and a buffer.

14. (Previously Presented) A semiconductor device according to claim 6, wherein the data line driver circuit comprises a shift register, NAND circuits, a level shifter and a buffer.

15. (Previously Presented) A semiconductor device according to claim 7, wherein the data line driver circuit further comprises a shift register, a level shifter and a buffer.

16. (Previously Presented) A semiconductor device according to claim 8, wherein the data line driver circuit comprises a shift register, NAND circuits, a level shifter and a buffer.

17. (Previously Presented) A semiconductor device according to claim 9, wherein the data line driver circuit further comprises a shift register, a level shifter and a buffer.

18. (Previously Presented) A semiconductor device according to claim 2, wherein the substrate comprises glass.

19. (Previously Presented) A semiconductor device according to claim 3, wherein the substrate comprises glass.

20. (Previously Presented) A semiconductor device according to claim 4, wherein the substrate comprises glass.

21. (Previously Presented) A semiconductor device according to claim 5, wherein the substrate comprises glass.

22. (Previously Presented) A semiconductor device according to claim 6, wherein the substrate comprises glass.

23. (Previously Presented) A semiconductor device according to claim 7, wherein the substrate comprises glass.

24. (Previously Presented) A semiconductor device according to claim 8, wherein the substrate comprises glass.

25. (Previously Presented) A semiconductor device according to claim 9, wherein the substrate comprises glass.

26. (Currently Amended) A semiconductor device according to claim 6, wherein the first and second thin film transistor ~~comprises~~ transistors comprise polycrystalline silicon film.

27. (Currently Amended) A semiconductor device according to claim 7, wherein the first and second thin film transistor ~~comprises~~ transistors comprise polycrystalline silicon film.

28. (Currently Amended) A semiconductor device according to claim 8, wherein the first and second thin film transistor comprises transistors comprise polycrystalline silicon film.

29. (Currently Amended) A semiconductor device according to claim 9, wherein the first and second thin film transistor comprises transistors comprise polycrystalline silicon film.

30. (Previously Presented) A semiconductor device according to claim 2, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

31. (Previously Presented) A semiconductor device according to claim 3, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

32. (Previously Presented) A semiconductor device according to claim 4, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

33. (Previously Presented) A semiconductor device according to claim 5, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

34. (Previously Presented) A semiconductor device according to claim 6, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

35. (Previously Presented) A semiconductor device according to claim 7, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

36. (Previously Presented) A semiconductor device according to claim 8, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

37. (Previously Presented) A semiconductor device according to claim 9, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle

type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

38. (New) A semiconductor device according to claim 2, wherein the first and second thin film transistors comprise polycrystalline silicon film.

39. (New) A semiconductor device according to claim 3, wherein the first and second thin film transistors comprise polycrystalline silicon film.

40. (New) A semiconductor device according to claim 4, wherein the first and second thin film transistors comprise polycrystalline silicon film.

41. (New) A semiconductor device according to claim 5, wherein the first and second thin film transistors comprise polycrystalline silicon film.

42. (New) A semiconductor device according to claim 2, wherein the insulating film comprises a silicon nitride film and a silicon oxide film.

43. (New) A semiconductor device according to claim 3, wherein the insulating film comprises a silicon nitride film and a silicon oxide film.

44. (New) A semiconductor device according to claim 4, wherein the insulating film comprises a silicon nitride film and a silicon oxide film.

45. (New) A semiconductor device according to claim 5, wherein the insulating film comprises a silicon nitride film and a silicon oxide film.

46. (New) A semiconductor device according to claim 6, wherein the first insulating film comprises a silicon nitride film and a silicon oxide film and the second insulating film comprises an organic resin film selected from the group consisting of polyimide, acryl and polyimideamide.

47. (New) A semiconductor device according to claim 7, wherein the first insulating film comprises a silicon nitride film and a silicon oxide film and the second insulating film comprises an organic resin film selected from the group consisting of polyimide, acryl and polyimideamide.

48. (New) A semiconductor device according to claim 8, wherein the first insulating film comprises a silicon nitride film and a silicon oxide film and the second insulating film comprises an organic resin film selected from the group consisting of polyimide, acryl and polyimideamide.

49. (New) A semiconductor device according to claim 9, wherein the first insulating film comprises a silicon nitride film and a silicon oxide film and the second insulating film comprises an organic resin film selected from the group consisting of polyimide, acryl and polyimideamide.

50. (New) A semiconductor device according to claim 2, wherein the metal is titanium.

51. (New) A semiconductor device according to claim 3, wherein the metal is titanium.

52. (New) A semiconductor device according to claim 4, wherein the metal is titanium.

53. (New) A semiconductor device according to claim 5, wherein the metal is titanium.

54. (New) A semiconductor device according to claim 6, wherein the metal is titanium.

55. (New) A semiconductor device according to claim 7, wherein the metal is titanium.

56. (New) A semiconductor device according to claim 8, wherein the metal is titanium.

57. (New) A semiconductor device according to claim 9, wherein the metal is titanium.

58. (New) A semiconductor device according to claim 2, wherein the first thin film transistor has a triple gate electrode-structure.

59. (New) A semiconductor device according to claim 3, wherein the first thin film transistor has a triple gate electrode-structure.

60. (New) A semiconductor device according to claim 4, wherein the first thin film transistor has a triple gate electrode-structure.

61. (New) A semiconductor device according to claim 5, wherein the first thin film transistor has a triple gate electrode-structure.

62. (New) A semiconductor device according to claim 6, wherein the first thin film transistor has a triple gate electrode-structure.

63. (New) A semiconductor device according to claim 7, wherein the first thin film transistor has a triple gate electrode-structure.

64. (New) A semiconductor device according to claim 8, wherein the first thin film transistor has a triple gate electrode-structure.

65. (New) A semiconductor device according to claim 9, wherein the first thin film transistor has a triple gate electrode-structure.

66. (New) A semiconductor device according to claim 2, wherein the second thin film transistor has a maximum operating frequency of 16 MHz when the second thin film transistor has a channel length of 4 μm .

67. (New) A semiconductor device according to claim 3, wherein the second thin film transistor has a maximum operating frequency of 16 MHz when the second thin film transistor has a channel length of 4 μm .

68. (New) A semiconductor device according to claim 4, wherein the second thin film transistor has a maximum operating frequency of 16 MHz when the second thin film transistor has a channel length of 4 μm .

69. (New) A semiconductor device according to claim 5, wherein the second thin film transistor has a maximum operating frequency of 16 MHz when the second thin film transistor has a channel length of 4 μm .

70. (New) A semiconductor device according to claim 6, wherein the second thin film transistor has a maximum operating frequency of 16 MHz when the second thin film transistor has a channel length of 4 μm .

71. (New) A semiconductor device according to claim 7, wherein the second thin film transistor has a maximum operating frequency of 16 MHz when the second thin film transistor has a channel length of 4 μm .

72. (New) A semiconductor device according to claim 8, wherein the second thin film transistor has a maximum operating frequency of 16 MHz when the second thin film transistor has a channel length of 4 μm .

73. (New) A semiconductor device according to claim 9, wherein the second thin film transistor has a maximum operating frequency of 16 MHz when the second thin film transistor has a channel length of 4 μm .

74. (New) A semiconductor device according to claim 2, the semiconductor device is a liquid crystal display device having an antiferroelectric liquid crystal material.

75. (New) A semiconductor device according to claim 3, the semiconductor device is a liquid crystal display device having an antiferroelectric liquid crystal material.

76. (New) A semiconductor device according to claim 4, the semiconductor device is a liquid crystal display device having an antiferroelectric liquid crystal material.

77. (New) A semiconductor device according to claim 5, the semiconductor device is a liquid crystal display device having an antiferroelectric liquid crystal material.

78. (New) A semiconductor device according to claim 6, the semiconductor device is a liquid crystal display device having an antiferroelectric liquid crystal material.

79. (New) A semiconductor device according to claim 7, the semiconductor device is a liquid crystal display device having an antiferroelectric liquid crystal material.

80. (New) A semiconductor device according to claim 8, the semiconductor device is a liquid crystal display device having an antiferroelectric liquid crystal material.

81. (New) A semiconductor device according to claim 9, the semiconductor device is a liquid crystal display device having an antiferroelectric liquid crystal material.

82. (New) A semiconductor device according to claim 2, wherein the data line driver circuit comprises a D/A conversion circuit.

83. (New) A semiconductor device according to claim 3, wherein the data line driver circuit comprises a D/A conversion circuit.

84. (New) A semiconductor device according to claim 4, wherein the data line driver circuit comprises a D/A conversion circuit.

85. (New) A semiconductor device according to claim 5, wherein the data line driver circuit comprises a D/A conversion circuit.

86. (New) A semiconductor device according to claim 6, wherein the data line driver circuit comprises a D/A conversion circuit.

87. (New) A semiconductor device according to claim 7, wherein the data line driver circuit comprises a D/A conversion circuit.

88. (New) A semiconductor device according to claim 8, wherein the data line driver circuit comprises a D/A conversion circuit.

89. (New) A semiconductor device according to claim 9, wherein the data line driver circuit comprises a D/A conversion circuit.